

# M5M5V408BFP,TP,RT,KV

## 4194304-BIT (524288-WORD BY 8-BIT) CMOS STATIC RAM

### DESCRIPTION

The M5M5V408B is a family of low voltage 4-Mbit static RAMs organized as 524,288-words by 8-bit, fabricated by Mitsubishi's high-performance 0.25μm CMOS technology.

The M5M5V408B is suitable for memory applications where a simple interfacing, battery operating and battery backup are the important design objectives.

M5M5V408B is packaged in 32-pin plastic SOP, 32-pin plastic TSOP and 32-pin 8mm x 13.4mm STSOP packages. Two types of TSOPs and two types of STSOPs are available, M5M5V408BTP (normal-lead-bend TSOP), M5M5V408BRT (reverse-lead-bend TSOP), M5M5V408BKV (normal-lead-bend STSOP) and M5M5V408BKR (reverse-lead-bend STSOP). These two types TSOPs and two types STSOPs are suitable for a surface mounting on double-sided printed circuit boards.

From the point of operating temperature, the family is divided into three versions; "Standard", "W-version", and "I-version". Those are summarized in the part name table below.

### FEATURES

- Single +2.7~+3.6V power supply
- Small stand-by current: 0.3μA(3V,typ.)
- No clocks, No refresh
- Data retention supply voltage=2.0V to 3.6V
- All inputs and outputs are TTL compatible.
- Easy memory expansion by  $\bar{S}$
- Common Data I/O
- Three-state outputs: OR-tie capability
- $\bar{OE}$  prevents data contention in the I/O bus
- Process technology: 0.25μm CMOS
- Package:
  - M5M5V408BFP: 32 pin 525 mil SOP
  - M5M5V408BTP/RT: 32 PIN 400mil TSOP(II)
  - M5M5V408BKV/KR: 32 pin 8mm x13.4mm STSOP

### PART NAME TABLE

Version, Operating temperature	Part name (## stands for "FP","TP", "RT","KV"or"KR")	Power Supply	Access time max.	Stand-by current I <sub>cc</sub> (PD), V <sub>cc</sub> =3.0V						Active current I <sub>cc1</sub> (3.0V, typ.)
				typical *		Ratings (max.)				
				25°C	40°C	25°C	40°C	70°C	85°C	
Standard 0 ~ +70°C	M5M5V408B## -70L	2.7 ~ 3.6V	70ns	---	---	---	---	30μA	---	30mA (10MHz)  5mA (1MHz)
	M5M5V408B## -85L		85ns	---	---	---	---	---		
	M5M5V408B## -70H	2.7 ~ 3.6V	70ns	0.3μA	1μA	1μA	3μA	15μA	---	
	M5M5V408B## -85H		85ns	---	---	---	---	---		
W-version -20 ~ +85°C	M5M5V408B## -70LW	2.7 ~ 3.6V	70ns	---	---	---	---	30μA	60μA	
	M5M5V408B## -85LW		85ns	---	---	---	---	---		
	M5M5V408B## -70HW	2.7 ~ 3.6V	70ns	0.3μA	1μA	1μA	3μA	15μA	30μA	
	M5M5V408B## -85HW		85ns	---	---	---	---	---		
I-version -40 ~ +85°C	M5M5V408B## -70LI	2.7 ~ 3.6V	70ns	---	---	---	---	30μA	60μA	
	M5M5V408B## -85LI		85ns	---	---	---	---	---		
	M5M5V408B## -70HI	2.7 ~ 3.6V	70ns	0.3μA	1μA	1μA	3μA	15μA	30μA	
	M5M5V408B## -85HI		85ns	---	---	---	---	---		

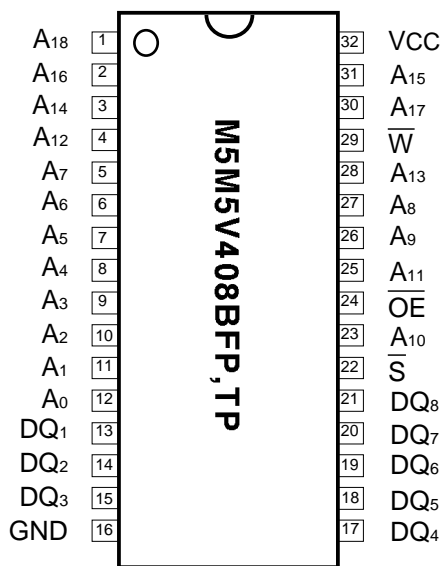
\* "typical" parameter is sampled, not 100% tested.

# M5M5V408BFP,TP,RT,KV

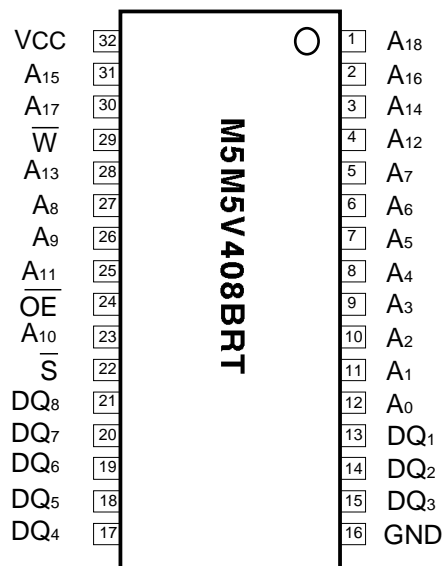
4194304-BIT (524288-WORD BY 8-BIT) CMOS STATIC RAM

## PIN CONFIGURATION (TOP VIEW)

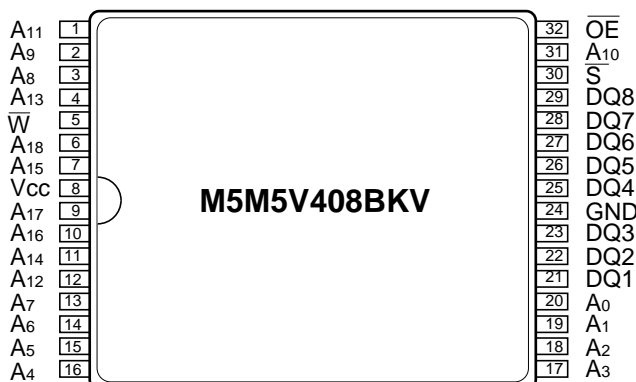
Pin	Function
A0 ~ A18	Address input
DQ1 ~ DQ8	Data input / output
$\overline{S}$	Chip select input
$\overline{W}$	Write control input
$\overline{OE}$	Output inable input
Vcc	Power supply
GND	Ground supply



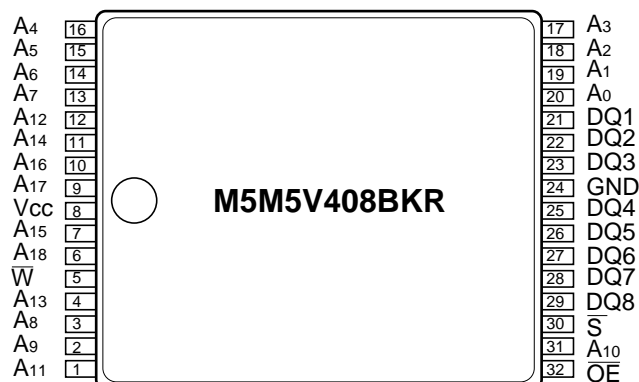
Outline 32P2M-A (FP)  
32P3Y-H (TP)



Outline 32P3Y-J (RT)



Outline 32P3K-B



Outline 32P3K-C

# M5M5V408BFP,TP,RT,KV

## 4194304-BIT (524288-WORD BY 8-BIT) CMOS STATIC RAM

### FUNCTION

The M5M5408BFP,TP,RT,KV,KR is organized as 524,288-words by 8-bit. These devices operate on a single +2.7~3.6V power supply, and are directly TTL compatible to both input and output. Its fully static circuit needs no clocks and no refresh, and makes it useful.

A write operation is executed during the  $\overline{S}$  low and  $\overline{W}$  low overlap time. The address(A0~A18) must be set up before the write cycle

A read operation is executed by setting  $\overline{W}$  at a high level and  $\overline{OE}$  at a low level while S are in an active state( $\overline{S}=L$ ).

When setting  $\overline{S}$  at a high level, the chips are in a non-selectable mode in which both reading and writing are disabled. In this mode, the output stage is in a high-impedance state, allowing OR-tie with other chips. Setting the  $\overline{OE}$  at a high level, the output stage is in a high-impedance state, and the data bus contention problem in the write cycle is eliminated.

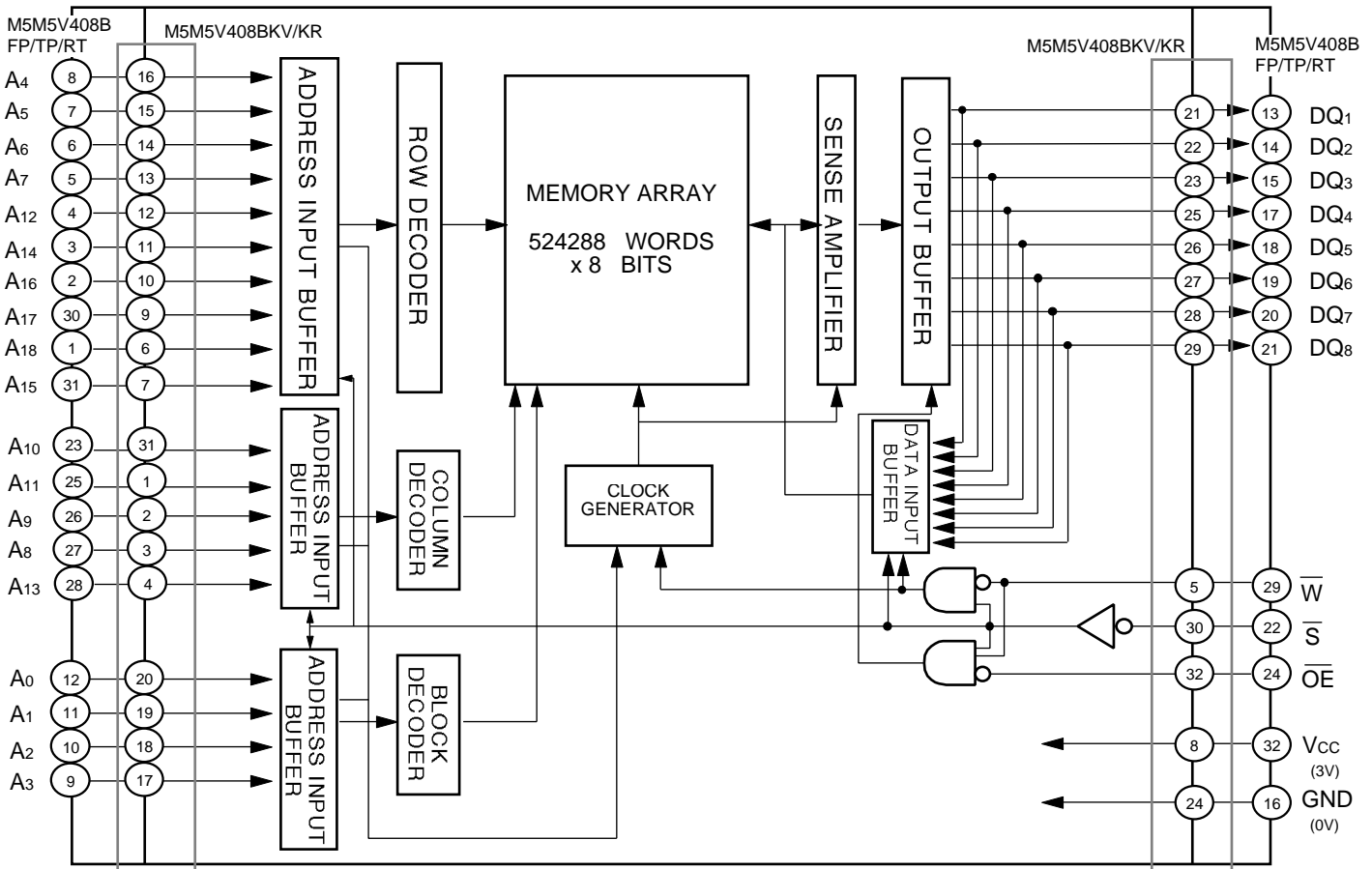
The power supply current is reduced as low as 0.3 $\mu$ A(25°C, typical), and the memory data can be held at +2V power supply, enabling battery back-up operation during power failure or power-down operation in the non-selected mode.

### FUNCTION TABLE

$\overline{S}$	$\overline{W}$	$\overline{OE}$	Mode	DQ	I <sub>cc</sub>
H	X	X	Non selection	High-impedance	Standby
L	L	X	Write	Data input (D)	Active
L	H	L	Read	Data output (Q)	Active
L	H	H	Read	High-impedance	Active

Pin	Function
A0 ~ A18	Address input
DQ1 ~ DQ8	Data input / output
$\overline{S}$	Chip select input
$\overline{W}$	Write control input
$\overline{OE}$	Output inable input
V <sub>cc</sub>	Power supply
GND	Ground supply

### BLOCK DIAGRAM



**M5M5V408BFP,TP,RT,KV****4194304-BIT (524288-WORD BY 8-BIT) CMOS STATIC RAM****ABSOLUTE MAXIMUM RATINGS**

Symbol	Parameter	Conditions	Ratings	Units
V <sub>CC</sub>	Supply voltage	With respect to GND	-0.5* ~ +4.6	V
V <sub>I</sub>	Input voltage	With respect to GND	-0.5* ~ V <sub>CC</sub> + 0.5	
V <sub>O</sub>	Output voltage	With respect to GND	0 ~ V <sub>CC</sub>	
P <sub>d</sub>	Power dissipation	T <sub>a</sub> =25°C	700	mW
T <sub>a</sub>	Operating temperature	Standard (-L, -H)	0 ~ +70	°C
		W-version (-LW, -HW)	-20 ~ +85	
		I-version (-LI, -HI)	-40 ~ +85	
T <sub>stg</sub>	Storage temperature		-65 ~ 150	°C

\* -3.0V in case of AC (Pulse width 30ns)

**DC ELECTRICAL CHARACTERISTICS**(V<sub>CC</sub>=2.7 ~ 3.6V, unless otherwise noted)

Symbol	Parameter	Conditions	Limits			Units		
			Min	Typ	Max			
V <sub>IH</sub>	High-level input voltage		2.2		V <sub>CC</sub> +0.3V	V		
V <sub>IL</sub>	Low-level input voltage		-0.3*		0.6			
V <sub>OH1</sub>	High-level output voltage 1	I <sub>OH</sub> = -0.5mA	2.4					
V <sub>OH2</sub>	High-level output voltage 2	I <sub>OH</sub> = -0.05mA	V <sub>CC</sub> -0.5V					
V <sub>OL</sub>	Low-level output voltage	I <sub>OL</sub> =2mA			0.4			
I <sub>I</sub>	Input leakage current	V <sub>I</sub> =0 ~ V <sub>CC</sub>			±1	μA		
I <sub>O</sub>	Output leakage current	$\bar{S}=V_{IH}$ or $\bar{OE}=V_{IH}$ , V <sub>I/O</sub> =0 ~ V <sub>CC</sub>			±1	μA		
I <sub>CC1</sub>	Active supply current (AC, CMOS-level)	$\bar{S}$ 0.2V Output-open Other inputs 0.2V or V <sub>CC</sub> -0.2V	f=10MHz	-	30	40	mA	
			f=1MHz	-	5	7		
I <sub>CC2</sub>	Active supply current (AC, TTL-level)	$\bar{S}=V_{IL}$ Output-open Other inputs=V <sub>IH</sub> or V <sub>IL</sub>	f=10MHz	-	30	40	mA	
			f=1MHz	-	5	7		
I <sub>CC3</sub>	Stand by supply current (CMOS-level input)	V <sub>CC</sub> =3.6V, max. $\bar{S}$ V <sub>CC</sub> -0.2V Other inputs=0~V <sub>CC</sub>	-LW, -LI	+85°C	-	-	80	μA
			-L, -LW, -LI	+70°C	-	-	40	
			-HW, -HI	+85°C	-	-	40	
			-H, -HW, -HI	+70°C	-	-	20	
				+40°C	-	1	5	
			-H	0 ~ +25°C	-	0.3	2	
			-HW	-20 ~ +25°C	-	0.3	2	
I <sub>CC4</sub>	Stand by supply current (TTL-level input)	$\bar{S}=V_{IH}$ , Other inputs= 0 ~ V <sub>CC</sub>				0.5	mA	

Note 1: Direction for current flowing into IC is indicated as positive (no mark)

\* -3.0V in case of AC (Pulse width 30ns)

Note 2: Typical value is for V<sub>CC</sub>=3.0V**CAPACITANCE**(V<sub>CC</sub>=2.7 ~ 3.6V, unless otherwise noted)

Symbol	Parameter	Conditions	Limits			Units
			Min	Typ	Max	
C <sub>I</sub>	Input capacitance	V <sub>I</sub> =GND, V <sub>I</sub> =25mVrms, f=1MHz			8	pF
C <sub>O</sub>	Output capacitance	V <sub>O</sub> =GND, V <sub>O</sub> =25mVrms, f=1MHz			10	



# M5M5V408BFP,TP,RT,KV

## 4194304-BIT (524288-WORD BY 8-BIT) CMOS STATIC RAM

### AC ELECTRICAL CHARACTERISTICS (V<sub>CC</sub>=2.7 ~ 3.6V, unless otherwise noted)

#### (1) TEST CONDITIONS

Supply voltage	2.7V~3.6V
Input pulse	V <sub>IH</sub> =2.4V, V <sub>IL</sub> =0.4V
Input rise time and fall time	5ns
Reference level	V <sub>OH</sub> =V <sub>OL</sub> =1.5V Transition is measured ±500mV from steady state voltage.(for t <sub>en</sub> ,t <sub>dis</sub> )
Output loads	Fig.1,CL=30pF CL=5pF (for t <sub>en</sub> ,t <sub>dis</sub> )

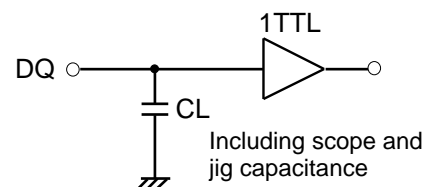


Fig.1 Output load

#### (2) READ CYCLE

Symbol	Parameter	Limits				Units
		M5M5V408B FP,TP,RT,KV,KR-70		M5M5V408B FP,TP,RT,KV,KR-85		
		Min	Max	Min	Max	
t <sub>CR</sub>	Read cycle time	70		85		ns
t <sub>a(A)</sub>	Address access time		70		85	ns
t <sub>a(S)</sub>	Chip select access time		70		85	ns
t <sub>a(OE)</sub>	Output enable access time		35		45	ns
t <sub>dis(S)</sub>	Output disable time after $\bar{S}$ high		25		30	ns
t <sub>dis(OE)</sub>	Output disable time after $\overline{OE}$ high		25		30	ns
t <sub>en(S)</sub>	Output enable time after $\bar{S}$ low	10		10		ns
t <sub>en(OE)</sub>	Output enable time after $\overline{OE}$ low	5		5		ns
t <sub>v(A)</sub>	Data valid time after address	10		10		ns

#### (3) WRITE CYCLE

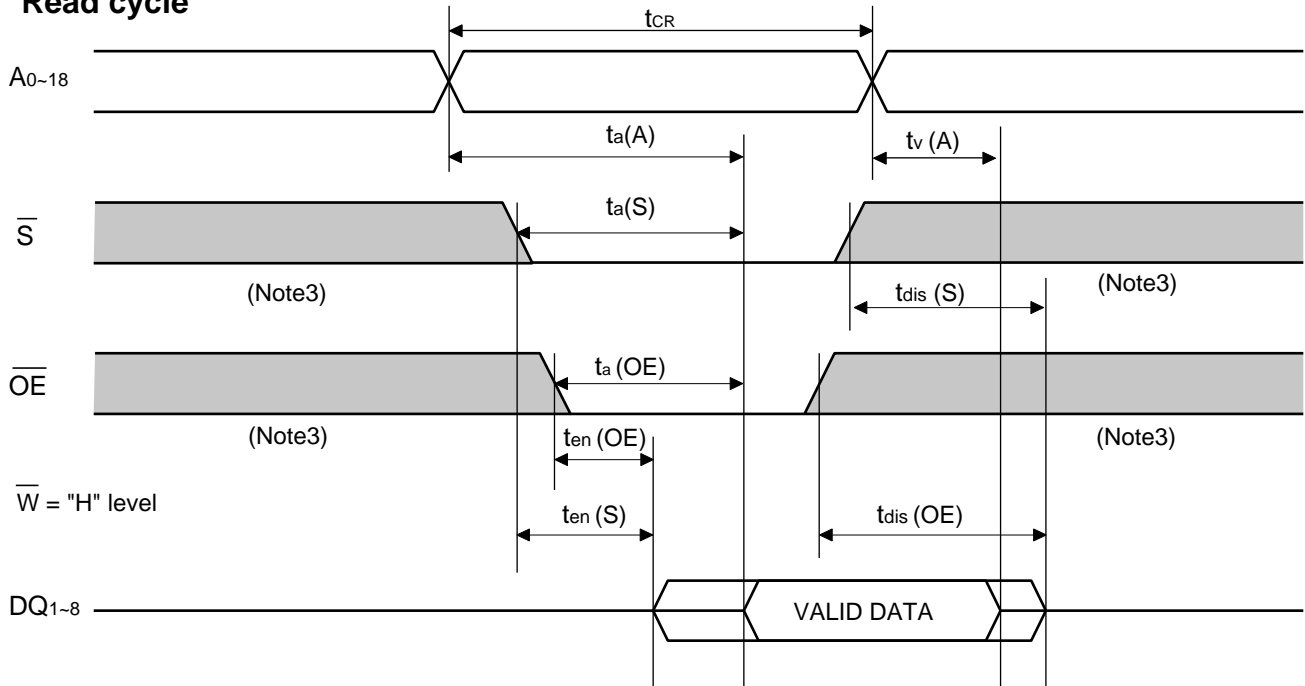
Symbol	Parameter	Limits				Units
		M5M5V408B FP,TP,RT,KV,KR-70		M5M5V408B FP,TP,RT,KV,KR-85		
		Min	Max	Min	Max	
t <sub>CW</sub>	Write cycle time	70		85		ns
t <sub>w(W)</sub>	Write pulse width	55		60		ns
t <sub>su(A)</sub>	Address set up time	0		0		ns
t <sub>su(A-WH)</sub>	Address set up time with respect to $\bar{W}$ high	65		70		ns
t <sub>su(S)</sub>	Chip select set up time	65		70		ns
t <sub>su(D)</sub>	Data set up time	35		35		ns
t <sub>h(D)</sub>	Data hold time	0		0		ns
t <sub>rec(W)</sub>	Write recovery time	0		0		ns
t <sub>dis(W)</sub>	Output disable time after $\bar{W}$ low		25		30	ns
t <sub>dis(OE)</sub>	Output disable time after $\overline{OE}$ high		25		30	ns
t <sub>en(W)</sub>	Output enable time after $\bar{W}$ high	5		5		ns
t <sub>en(OE)</sub>	Output enable time after $\overline{OE}$ low	5		5		ns

# M5M5V408BFP,TP,RT,KV

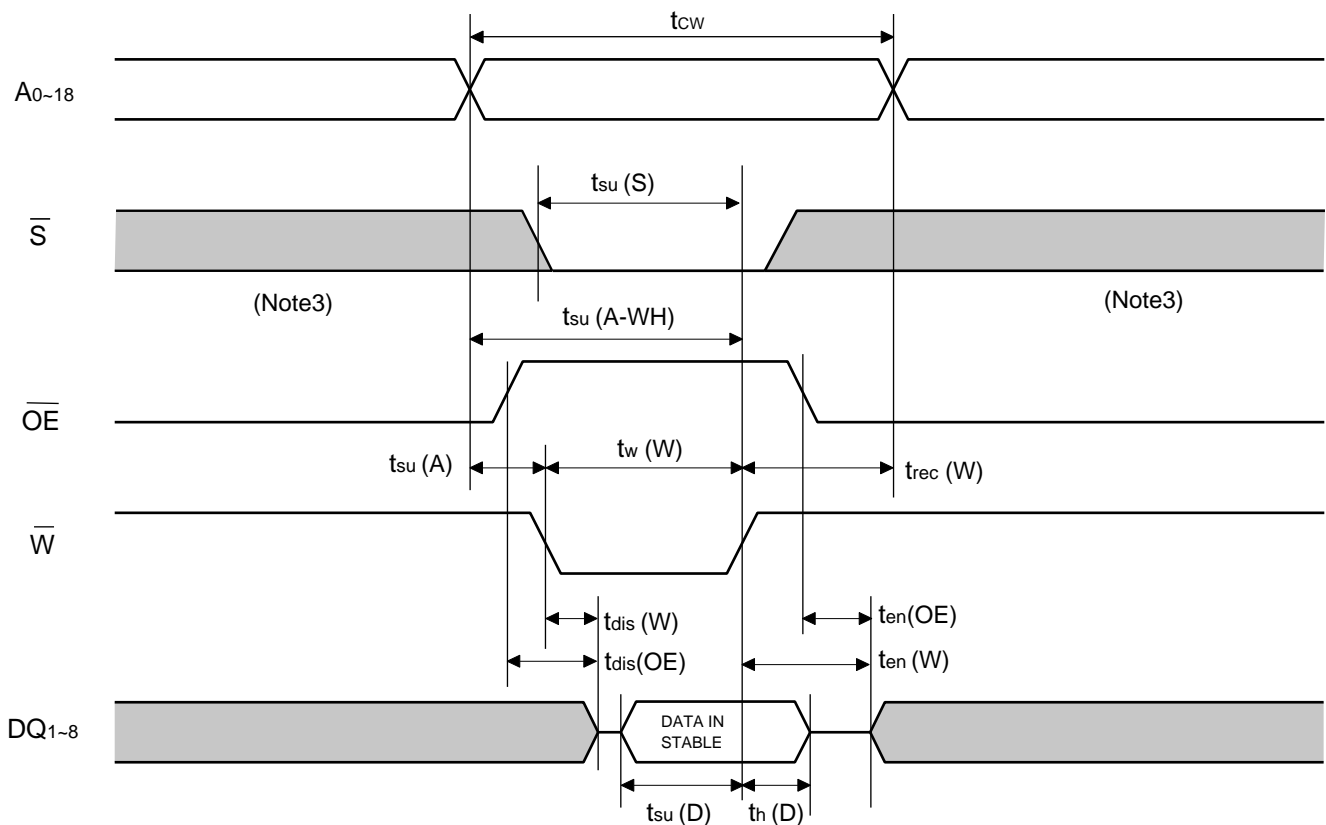
4194304-BIT (524288-WORD BY 8-BIT) CMOS STATIC RAM

## (4)TIMING DIAGRAMS

### Read cycle



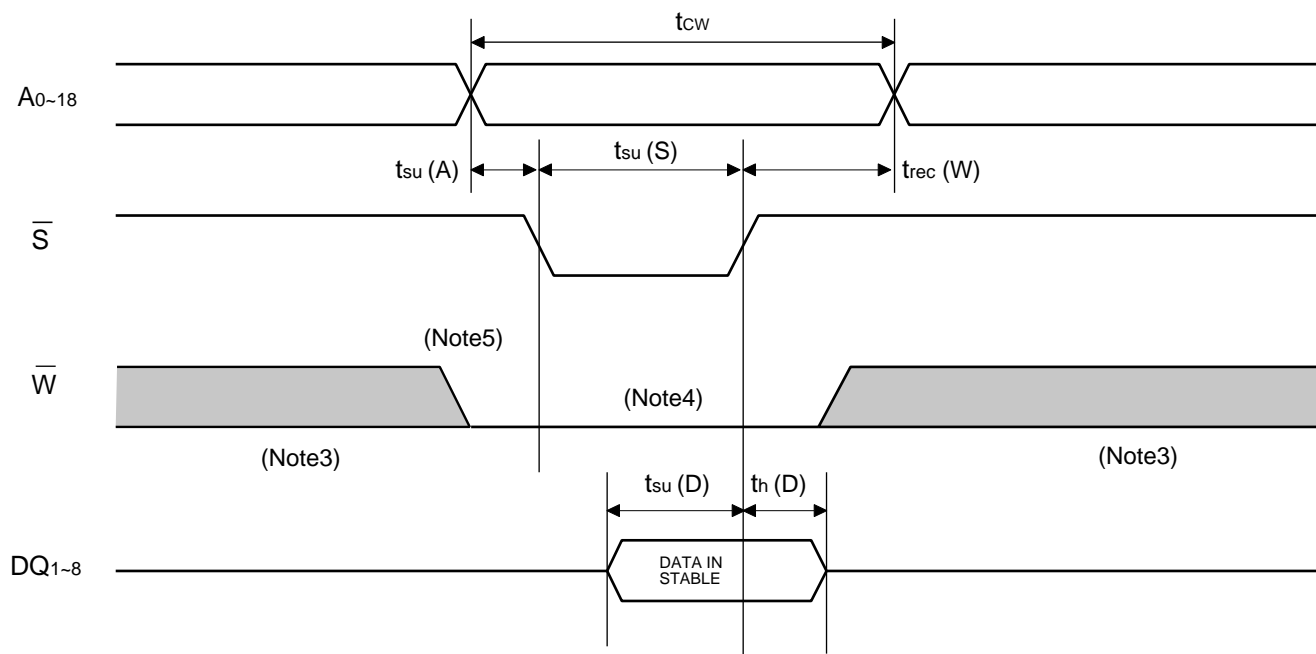
### Write cycle ( $\bar{W}$ control mode)



# M5M5V408BFP,TP,RT,KV

4194304-BIT (524288-WORD BY 8-BIT) CMOS STATIC RAM

## Write cycle ( $\overline{S}$ control mode)



Note 3: Hatching indicates the state is "don't care".

Note 4: A Write occurs during the overlap of a low  $\overline{S}$  and a low  $\overline{W}$ .

Note 5: If  $\overline{W}$  goes low simultaneously with or prior to  $\overline{S}$ , the output remains in the high impedance state.

Note 6: Don't apply inverted phase signal externally when DQ pin is in output mode.

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## POWER DOWN CHARACTERISTICS

### (1) ELECTRICAL CHARACTERISTICS

Symbol	Parameter	Test conditions	Limits			Units		
			Min	Typ	Max			
V <sub>cc</sub> (PD)	Power down supply voltage		2.0			V		
V <sub>i</sub> ( $\bar{S}$ )	Chip select input $\bar{S}$		2.0			V		
I <sub>cc</sub> (PD)	Power down supply current	V <sub>cc</sub> =3.0V, $\bar{S}$ V <sub>cc</sub> -0.2V, Other inputs = 0 ~ V <sub>cc</sub>	-LW, -LI	+85°C	-	-	60	μA
			-L, -LW, -LI	+70°C	-	-	30	μA
			-HW, -HI	+85°C	-	-	30	μA
			-H, -HW, -HI	+70°C	-	-	15	μA
				+40°C	-	1	3	μA
			-H	0 ~ +25°C	-	0.3	1	μA
			-HW	-20 ~ +25°C	-	0.3	1	μA
-HI	-40 ~ +25°C	-	0.3	1	μA			

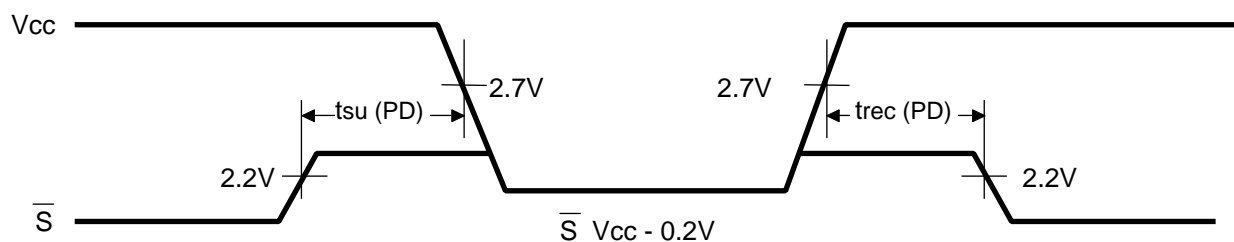
Typical value is based on sampling.

### (2) TIMING REQUIREMENTS

Symbol	Parameter	Test conditions	Limits			Units
			Min	Typ	Max	
t <sub>su</sub> (PD)	Power down set up time		0			ns
t <sub>rec</sub> (PD)	Power down recovery time		5			ms

### (3) TIMING DIAGRAM

$\bar{S}$  control mode





**M5M5V408BFP,TP,RT,KV****4194304-BIT (524288-WORD BY 8-BIT) CMOS STATIC RAM**

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**Revision History**

<u>Revision No.</u>	<u>History</u>	<u>Date</u>	<u>Remarks</u>
K0.1e	The first edition	'98.3.05	Preliminary
K0.2e	Added M5M5V408BFP/TP/RT	'98.7.30	Preliminary
K1.0e	The first product version	'98.9.7	---
K2.0e	1) Speed items revised: 70ns added and 100ns deleted		
	2) lcc3 and lcc(PD) limits revised	'99.3.10	---

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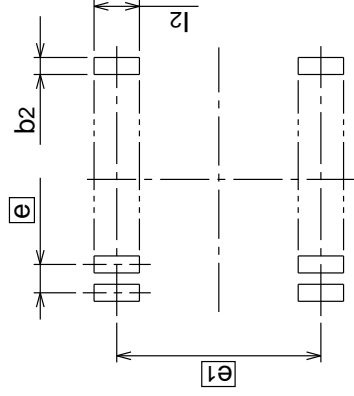
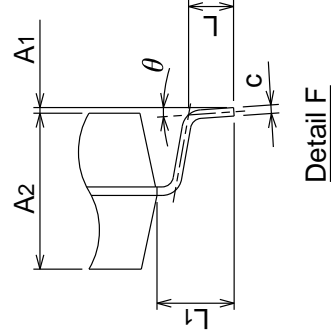
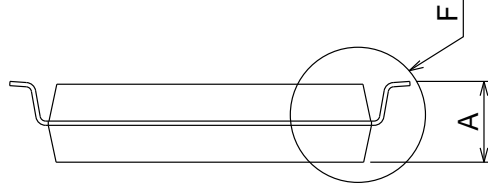
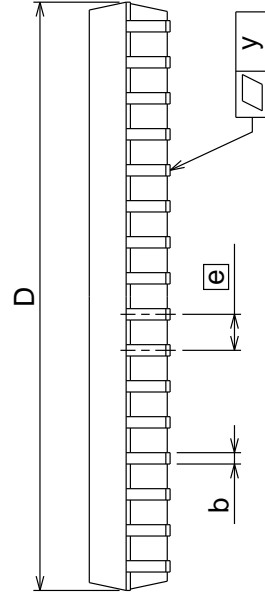
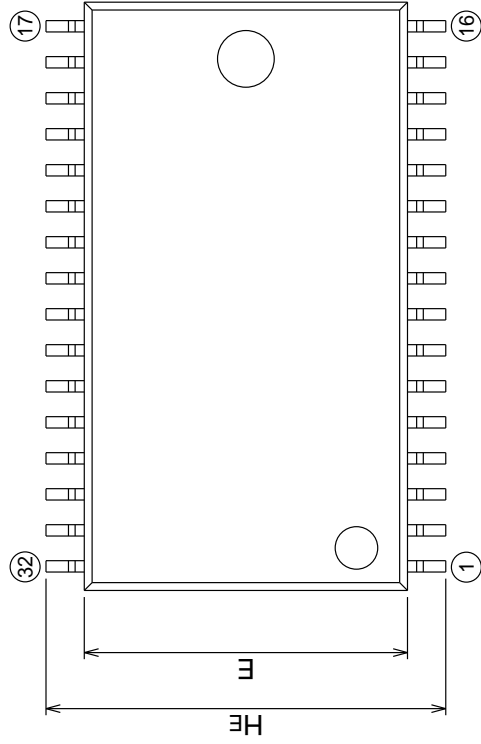
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# 32P2M-A

# Plastic 32pin 525mil SOP

EIAJ Package Code SOP32-P-525-1.27	JEDEC Code -	Weight(g) 1.29	Lead Material Alloy 42
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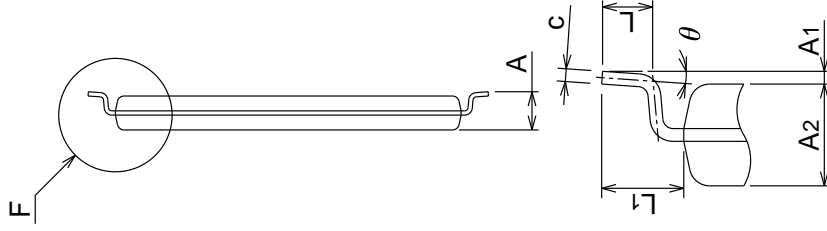
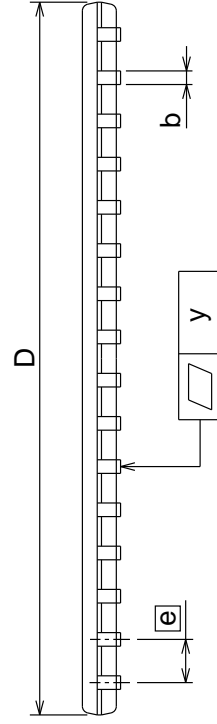
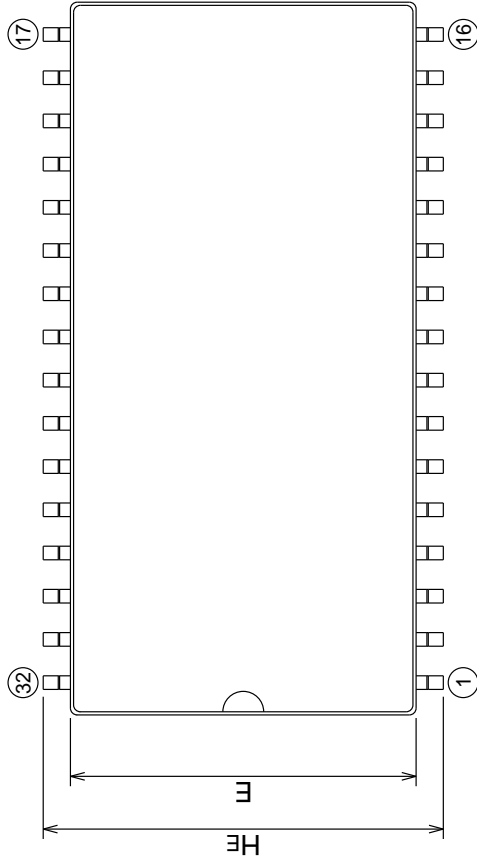
Recommended Mount Pad

Symbol	Dimension in Millimeters		
	Min	Nom	Max
A	-	-	3.05
A1	0	0.1	0.2
A2	-	2.75	-
b	0.35	0.4	0.5
c	0.13	0.15	0.2
D	20.55	20.75	20.95
E	11.3	11.4	11.5
e	-	1.27	-
HE	13.8	14.1	14.4
L	0.6	0.8	1.0
L1	-	1.35	-
y	-	-	0.15
$\theta$	0°	-	8°
b2	-	0.76	-
e1	-	13.34	-
l2	1.27	-	-

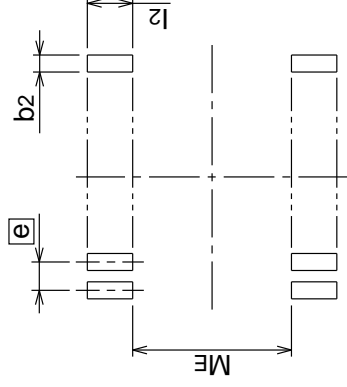
# 32P3Y-H

# Plastic 32pin 400mil TSOP (II)

EIAJ Package Code TSOPII32-P-400-1.27	JEDEC Code -	Weight(g) 0.53	Lead Material Alloy 42
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Detail F



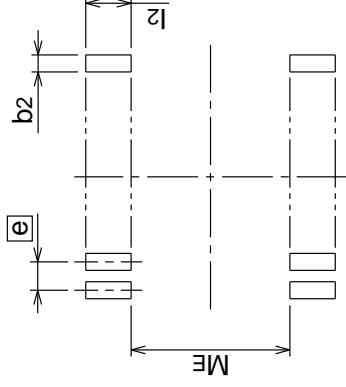
Recommended Mount Pad

Symbol	Dimension in Millimeters		
	Min	Nom	Max
A	-	-	1.2
A1	0.05	0.125	0.2
A2	-	1.0	-
b	0.35	0.4	0.5
c	0.105	0.125	0.175
D	20.85	20.95	21.05
E	10.06	10.16	10.26
e	-	1.27	-
HE	11.56	11.76	11.96
L	0.4	0.5	0.6
L1	-	0.8	-
y	-	-	0.1
$\theta$	0°	-	10°
ME	-	10.36	-
l2	0.9	-	-
b2	-	0.76	-

# 32P3Y-J

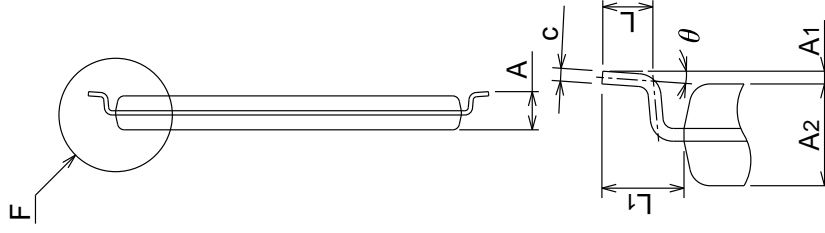
# Plastic 32pin 400mil TSOP (II)

EIAJ Package Code TSOPII32-P-400-1.27	JEDEC Code -	Weight(g) 0.53	Lead Material Alloy 42
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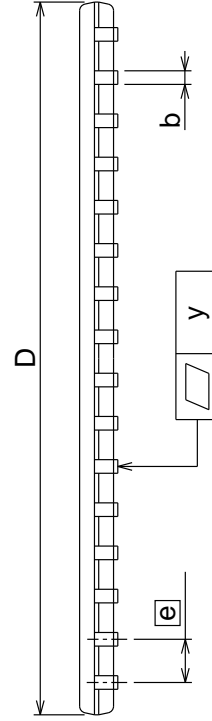
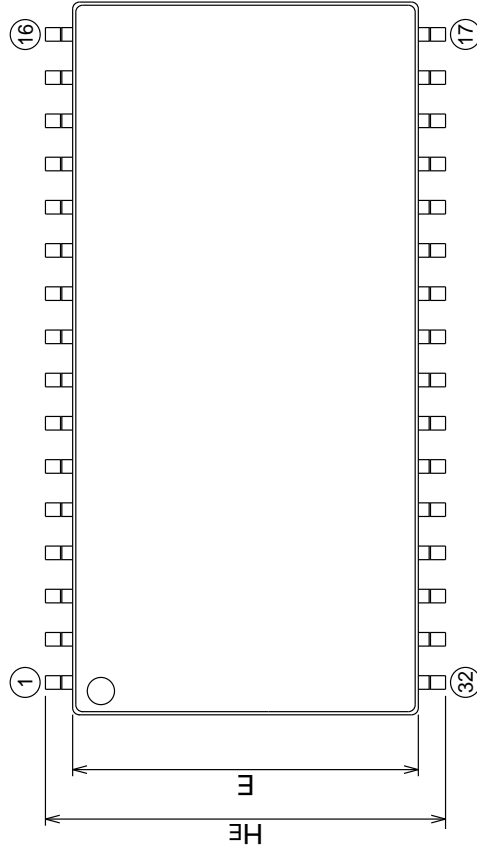


Recommended Mount Pad

Symbol	Dimension in Millimeters		
	Min	Nom	Max
A	-	-	1.2
A1	0.05	0.125	0.2
A2	-	1.0	-
b	0.35	0.4	0.5
c	0.105	0.125	0.175
D	20.85	20.95	21.05
E	10.06	10.16	10.26
e	-	1.27	-
HE	11.56	11.76	11.96
L	0.4	0.5	0.6
L1	-	0.8	-
y	-	-	0.1
$\theta$	0°	-	10°
ME	-	10.36	-
l2	0.9	-	-
b2	-	0.76	-



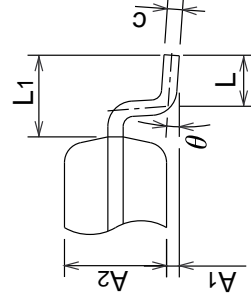
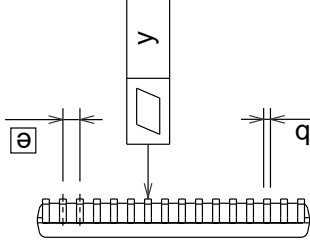
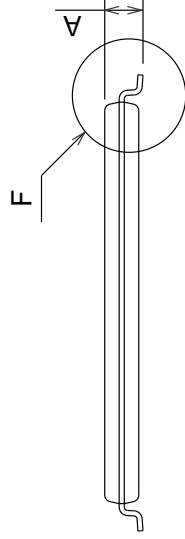
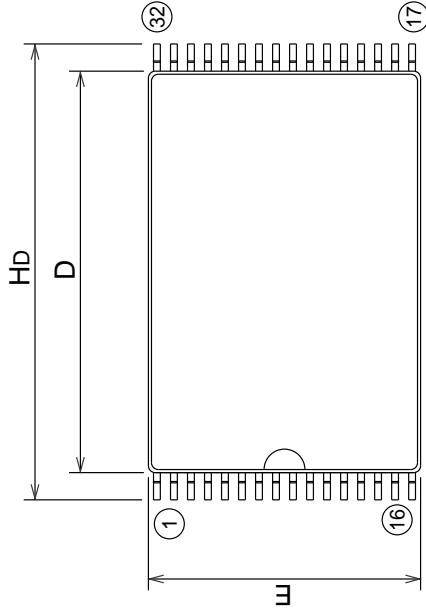
Detail F



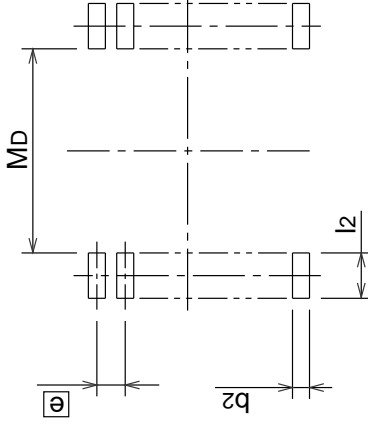
# 32P3K-B

# Plastic 32pin 8X13.4mm TSOP(I)

EIAJ Package Code	JEDEC Code	Weight(g)	Lead Material
-	-	-	Alloy 42



Detail F



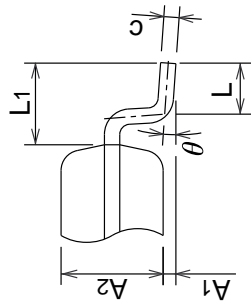
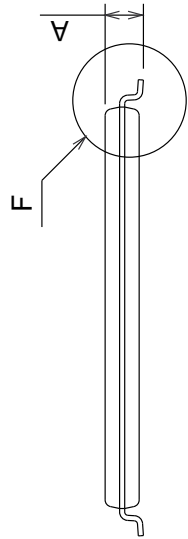
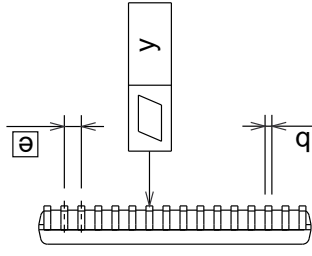
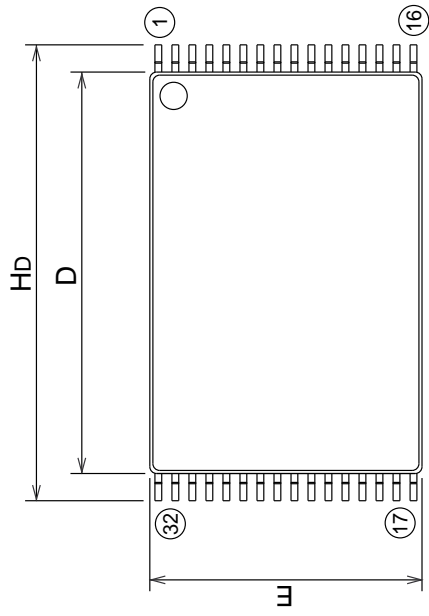
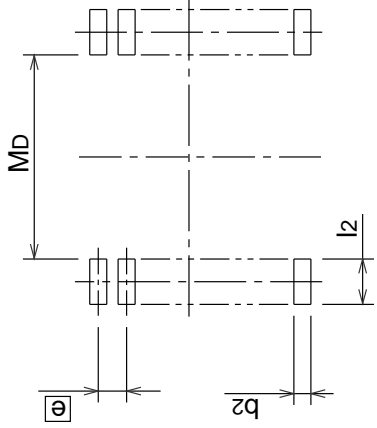
Recommended Mount Pad

Symbol	Dimension in Millimeters		
	Min	Nom	Max
A	-	-	1.2
A1	0.05	0.125	0.2
A2	-	1.0	-
b	0.15	0.2	0.3
c	0.13	0.15	0.2
D	11.7	11.8	11.9
E	7.9	8.0	8.1
e	-	0.5	-
HD	13.2	13.4	13.6
L	0.4	0.5	0.6
L1	-	0.8	-
y	-	-	0.1
$\theta$	0°	-	10°
b2	-	0.225	-
l2	0.9	-	-
MD	-	12.0	-

# 32P3K-C

# Plastic 32pin 8X13.4mm TSOP(I)

EIAJ Package Code	JEDEC Code	Weight(g)	Lead Material
-	-	-	Alloy 42



Recommended Mount Pad

Symbol	Dimension in Millimeters		
	Min	Nom	Max
A	-	-	1.2
A1	0.05	0.125	0.2
A2	-	1.0	-
b	0.15	0.2	0.3
c	0.13	0.15	0.2
D	11.7	11.8	11.9
E	7.9	8.0	8.1
e	-	0.5	-
HD	13.2	13.4	13.6
L	0.4	0.5	0.6
L1	-	0.8	-
y	-	-	0.1
theta	0°	-	10°
b2	-	0.225	-
l2	0.9	-	-
MD	-	12.0	-

Detail F

This datasheet has been download from:

[www.datasheetcatalog.com](http://www.datasheetcatalog.com)

Datasheets for electronics components.